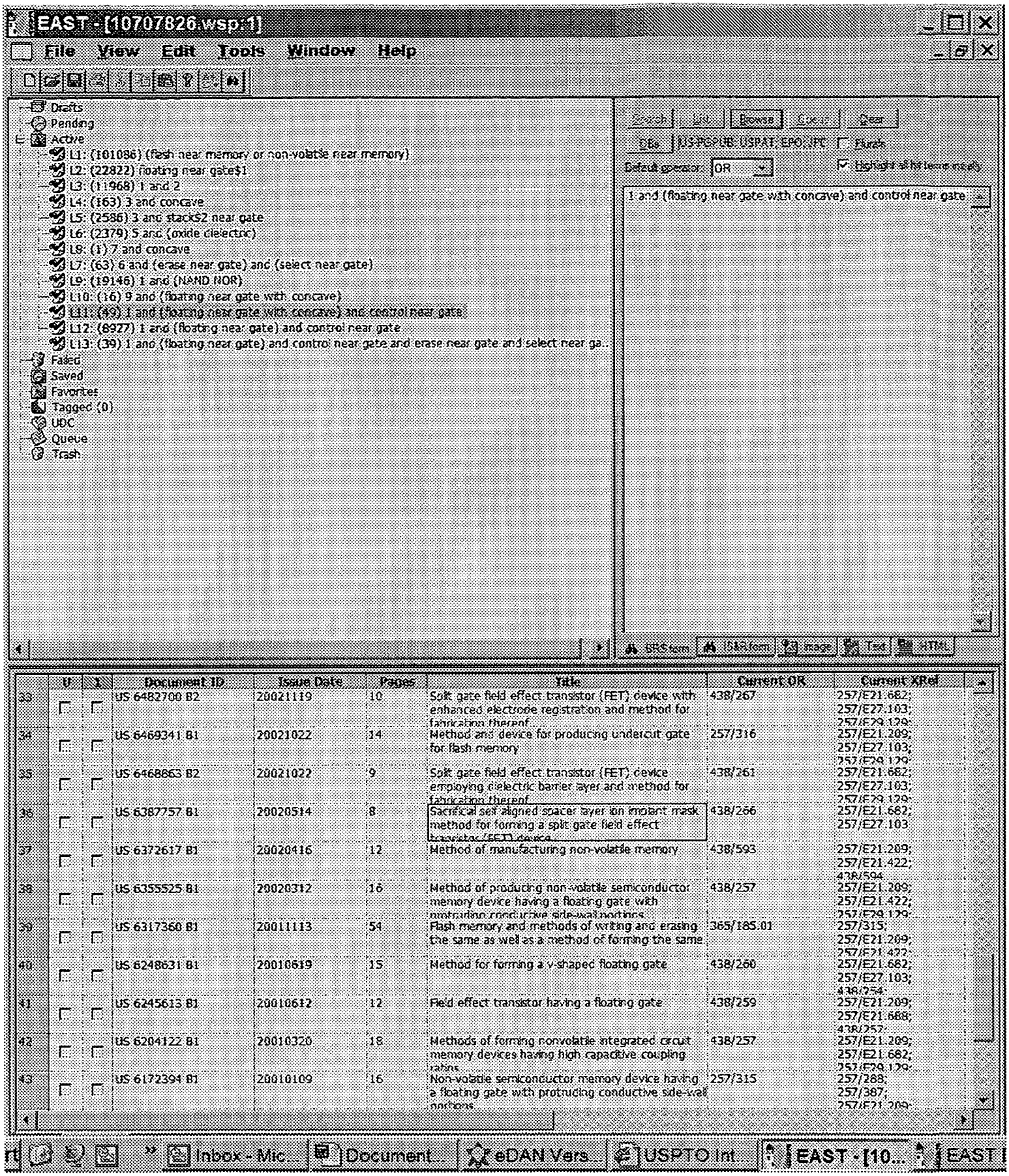
EAST - [10707826.wsp:1]
File View Edit Tools Window Help
Drafts
Pending
Active
L1: (101086) (flash near memory or non-volatile near memory)
L2: (22822) floating near gate$1
L3: (11968) 1 and 2
L4: (163) 3 and concave
L5: (2586) 3 and stack$2 near gate
L6: (2379) 5 and (oxide dielectric)
L8: (1) 7 and concave
L7: (63) 6 and (erase near gate) and (select near gate)
L9: (19146) 1 and (NAND NOR)
L10: (16) 9 and (floating near gate with concave)
L11: (49) 1 and (floating near gate with concave) and control near gate
L12: (8927) 1 and (floating near gate) and control near gate
L13: (39) 1 and (floating near gate) and control near gate and erase near gate and select near ga..
Failed
Saved
Favorites
Tagged (0)
UDC
Queue
Trash
Search
Browse
Clear
Default operator: OR
Highlight all hit terms initially
1 and (floating near gate with concave) and control near gate
Image
Text
HTML
U
I
Document ID
Issue Date
Pages
Title
Current OR
Current XRef
33 US 6482700 B2 20021119 10 Split gate field effect transistor (FET) device with enhanced electrode registration and method for fabrication thereof 438/267 257/E21.682; 257/E27.103; 257/E29.129
34 US 6469341 B1 20021022 14 Method and device for producing undercut gate for flash memory 257/316 257/E21.209; 257/E27.103; 257/E29.129
35 US 6468863 B2 20021022 9 Split gate field effect transistor (FET) device employing dielectric barrier layer and method for fabrication thereof 438/261 257/E21.682; 257/E27.103; 257/E29.129
36 US 6387757 B1 20020514 8 Sacrificial self aligned spacer layer ion implant mask method for forming a split gate field effect transistor (FET) device 438/266 257/E21.682; 257/E27.103
37 US 6372617 B1 20020416 12 Method of manufacturing non-volatile memory 438/593 257/E21.209; 257/E21.422; 438/594
38 US 6355525 B1 20020312 16 Method of producing non-volatile semiconductor memory device having a floating gate with protruding conductive side-wall portions 438/257 257/E21.209; 257/E21.422; 257/E29.129
39 US 6317360 B1 20011113 54 Flash memory and methods of writing and erasing the same as well as a method of forming the same 365/185.01 257/315; 257/E21.209; 257/E21.422
40 US 6248631 B1 20010619 15 Method for forming a v-shaped floating gate 438/260 257/E21.682; 257/E27.103; 438/254
41 US 6245613 B1 20010612 12 Field effect transistor having a floating gate 438/259 257/E21.209; 257/E21.688; 438/257
42 US 6204122 B1 20010320 18 Methods of forming nonvolatile integrated circuit memory devices having high capacitive coupling ratios 438/257 257/E21.209; 257/E21.682; 257/E29.129
43 US 6172394 B1 20010109 16 Non-volatile semiconductor memory device having a floating gate with protruding conductive side-wall portions 257/315 257/288; 257/367; 257/E21.209
Inbox - Mic...
Document...
eDAN Vers...
USPTO Int...
EAST - [10...
EAST